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| APPLICATION NO. | FILING DATE | FIRST NAMED INVENTOR | ATTORNEY DOCKET NO. | CONFIRMATION NO. |
|-----------------|--------------------------------------|----------------------|-------------------------|------------------|
| 09/842,000 | 04/26/2001 | Toru Otsubo | 503.39737X00 | 7052 |
| 20437 | 7590 12/20/2002 I TERRY STOUT ANI | KRAUS | EXAMINER | |
| SHITE 1800 | SEVENTEENTH STREE | CROWELL, ANNA M | | |
| ARLINGTON | , VA 22209 | | ART UNIT | PAPER NUMBER |
| | | | 1763 | \Box |
| | | | DATE MAILED: 12/20/2002 | f |

Please find below and/or attached an Office communication concerning this application or proceeding.

| • | | | | | |
|--|---|--|---|--|--|
| | | Application No. | Applicant(s) | | |
| | | 09/842,000 | OTSUBO, TORU | | |
| Office Action Summary | | Examiner | Art Unit | | |
| | | Michelle Crowell | 1763 | | |
| Period fo | The MAILING DATE of this communication or Reply | | | | |
| A SHO THE M - Exten after: - If the - If NO - Failur | ORTENED STATUTORY PERIOD FOR REMAILING DATE OF THIS COMMUNICATIOnsions of time may be available under the provisions of 37 CFS SIX (6) MONTHS from the mailing date of this communication period for reply specified above is less than thirty (30) days, a period for reply is specified above, the maximum statutory pere to reply within the set or extended period for reply will, by streply received by the Office later than three months after the med patent term adjustment. See 37 CFR 1.704(b). | IN. R 1.136(a). In no event, however, may a reply within the statutory minimum of thi nod will apply and will expire SIX (6) MOI | reply be timely filed ty (30) days will be considered timely. NTHS from the mailing date of this communication. BANDONED (35 U.S.C. § 133). | | |
| 1)⊠ | Responsive to communication(s) filed on | <u> 26 April 2001</u> . | | | |
| 2a)□ | This action is FINAL . 2b)⊠ | This action is non-final. | | | |
| 3)□ | Since this application is in condition for all closed in accordance with the practice un ion of Claims | lowance except for formal mader <i>Ex parte Quayle</i> , 1935 C | atters, prosecution as to the merits is .D. 11, 453 O.G. 213. | | |
| - | Claim(s) 1-3,7 and 8 is/are pending in the | application. | | | |
| -1/23 | 4a) Of the above claim(s) is/are with | drawn from consideration. | | | |
| | Claim(s) is/are allowed. | | | | |
| | Claim(s) <u>1-3,7 and 8</u> is/are rejected. | | | | |
| | Claim(s) is/are objected to. | | | | |
| | Claim(s) are subject to restriction a | nd/or election requirement. | | | |
| | tion Papers | | | | |
| 9)[| The specification is objected to by the Exar | miner. | | | |
| 10) | The drawing(s) filed on is/are: a) | accepted or b∖) objected to by | the Examiner. | | |
| | Applicant may not request that any objection | to the drawing(s) be held in abe | yance. See 37 CFR 1.85(a). | | |
| 11) | The proposed drawing correction filed on _ | | disapproved by the Examiner. | | |
| | If approved, corrected drawings are required | | | | |
| 12)[| The oath or declaration is objected to by th | e Examiner. | | | |
| Priority | under 35 U.S.C. §§ 119 and 120 | | | | |
| 13)⊠ | Acknowledgment is made of a claim for fo | oreign priority under 35 U.S.C | c. § 119(a)-(d) or (f). | | |
| а | ı)⊠ All b)□ Some * c)□ None of: | | | | |
| - | 1. Certified copies of the priority docu | ments have been received. | s | | |
| | 2. Certified copies of the priority documents have been received in Application No | | | | |
| * | Copies of the certified copies of the application from the Internation See the attached detailed Office action for | a list of the certified copies n | ot received. | | |
| 14) | Acknowledgment is made of a claim for do | mestic priority under 35 U.S. | C. § 119(e) (to a provisional application). | | |
| | a) The translation of the foreign language Acknowledgment is made of a claim for do | ge provisional application has | been received. | | |
| Attachme | | | | | |
| 2) No | otice of References Cited (PTO-892) otice of Draftsperson's Patent Drawing Review (PTO-94 formation Disclosure Statement(s) (PTO-1449) Paper N | 48) 5) Notice | ew Summary (PTO-413) Paper No(s) of Informal Patent Application (PTO-152) | | |
| | d Tradamark Office | | Part of Paper No. 7 | | |

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DETAILED ACTION

Specification

1a. The substitute specification filed November 29, 2001 has not been entered because it does not conform to 37 CFR 1.125(b)because: a marked up version is not provided (1), and a complete specification (non-marked up version) is not provided.

Claim Rejections - 35 USC § 112

- The following is a quotation of the second paragraph of 35 U.S.C. 112:
 The specification shall conclude with one or more claims particularly pointing out and distinctly claiming the subject matter which the applicant regards as his invention.
- 2. Claims 2, 3, 7, and 8 are rejected under 35 U.S.C. 112, second paragraph, as being indefinite for failing to particularly point out and distinctly claim the subject matter which applicant regards as the invention.
- 3. Claim 2, 7, and 8 recite the limitation, "a means to process plasma using the generated plasma" which is indefinite. The specification fails to specifically describe this means. Where is this limitation described in the specification?
- 4. Claim 3 recites the limitation, "said memory means" in lines 5 and 6. There is insufficient antecedent basis for this limitation in the claim.
- 5. Claim 7 recites the limitation, "a RF bias circuit to send RF current to the substrate to be processed is suspended with respect to the ground" which is indefinite. How is the RF bias circuit suspended with respect to the ground? What does "suspended with respect to the ground" mean? Where is this limitation described in the specification?

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6. Claim 8 recites the limitation, "means to control a RF current ratio" which is indefinite.

The specification fails to specifically describe this means. How does this means control RF current ration? Where is this limitation described in the specification?

Claim Rejections - 35 USC § 103

- 7. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:
 - (a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.
- 8. Claims 1, 2, 7 and 8 are rejected under 35 U.S.C. 103(a) as being unpatentable over Otsubo et al. (Japanese Patent Publication 11-260596) in view of Yamagata et al. (U.S. 5,362,358).

Referring to Drawing 1 and 16, and paragraphs [0113]-[0130], Otsubo discloses a plasma processing apparatus comprising an etching gas supply mechanism, an exhaust air mechanism [0114], a counterelectrodes 71a 71b 71c (capacitively coupled discharge means, plasma generating means, multiple RF current conducting means) [115], a coil 58 (magnetic field forming means) [0131], a signal generator 97, a capacitor 83, and a stage electrode 52. Each of the counterelectrodes 71a 71b 71c is mutually insulated by insulating materials 80a 80b 80c, thereby creating mutually isolated multiple conductors [0115]. Furthermore, the counterelectrodes 71a 71b 71c are grounded through low pass filters (not shown), and a high-frequency current from a bias power supply 56 is allowed to flow through each of the

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counterelectrodes 71a 71b 71c [0116]. Also, the bias power supply 56 (RF bias circuit) is supplied to the stage electrode 52 which sends a RF current to the substrate 55 [122]-[123].

A high-frequency voltage 81 and 82, whose phase can be shifted by a capacitor 83 (frequency displacement current control means), is supplied to the counterelectrodes 71, thereby generating electromagnetic waves. The power of electromagnetic waves radiates through the insulators and counterelectrodes (radio frequency displacement). A resonant circuit is formed via the insulators 80 and the capacitor 83. The signal generator 97 (electromagnetic wave power control means) controls the phase of the high-frequency signal [0130]. Alternately, the electromagnetic waves can be generated by antenna 11 [0041].

Specifically, the distribution of the plasma density can be controlled by controlling the radiated electromagnetic waves based on the adjustment of the phase of the high-frequency voltage supplied to the counterelectrodes 71. Moreover, the distribution of the plasma density due to capacitive coupled plasma can be controlled by controlling the outputs of the high frequency power supplies 81 and 82 (electromagnetic waver power control means) [0131].

Otsubo fails to specifically teach an electromagnetic wave power control means.

Referring to Figure 6 and column 5, lines 30-65, Yamagata teaches a motor speed controller (electromagnetic wave power control means) connected to variable capacitors 24 and 26 via a motor 80 (drive motor). A radio frequency (RF) power source 20 is provided between an impedance match network 22 and the ground. Selective application of RF power to the electrodes 12 and 14 is performed by controlling the capacitors 24 and 26. By controlling the variable capacitors 24 and 26, anisotropic or isotropic etching may be performed. Thus, it would have been obvious to one of ordinary skill in the art at the time of the invention to provide the

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capacitor of Otsubo with the motor and controller as taught by Yamagata. By controlling the variable capacitors 24 and 26, anisotropic or isotropic etching may be selectively performed.

9. Claim 3 is rejected under 35 U.S.C. 103(a) as being unpatentable over Otsubo et al. (Japanese Patent Publication 11-260596) in view of Yamagata et al. (U.S. 5,362,358) as applied to claims 1, 2, 7, and 8 above, and further in view of Misonoo et al. (Japanese Patent Publication 08-167588).

Otsubo fails to teach a means to store.

Referring to Drawing 1 and the abstract, Otsubo teaches a plasma treatment device comprising a plasma monitoring means 2, a comparison means 19, a memory means 18 and a current control means 16. The memory means 18 stores a plasma density distribution for a process. Plasma density distribution is controlled by the comparison means 17 and the current control means 16, thus uniformly treating the surface of a specimen with plasma. Thus, it would have been obvious to one of ordinary skill in the art at the time of the invention to provide the chamber of Otsubo with the memory means of Misonoo. This would store the information needed to plasma treat a substrate uniformly.

Conclusion

10. The prior art made of record and not relied upon is considered pertinent to applicant's disclosure.

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Any inquiry concerning this communication or earlier communications from the examiner should be directed to Michelle Crowell whose telephone number is (703) 305-1956. The examiner can normally be reached on M-F (8:00 - 4:30).

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Gregory Mills can be reached on (703) 308-1633. The fax phone numbers for the organization where this application or proceeding is assigned are (703) 872-9310 for regular communications and (703) 872-9311 for After Final communications.

Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the receptionist whose telephone number is (703) 308-0661.

AMC QWV C December 16, 2002